

HIGH-SPEED 3.3V 16K x 18 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

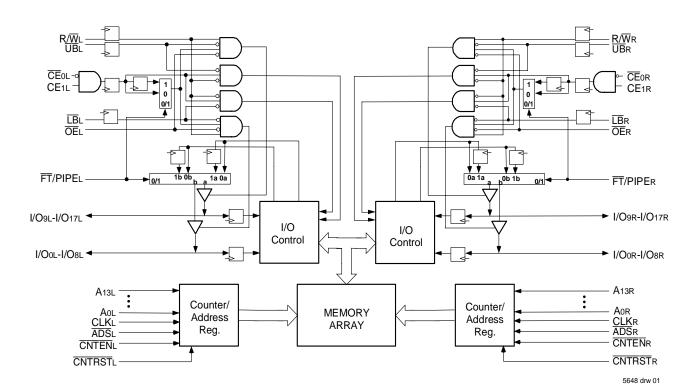
IDT70V9369L

Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 6/7.5/9/12ns (max.)
 - Industrial: 7.5ns (max.)
- Low-power operation
 - IDT70V9369L Active: 500mW (typ.) Standby: 1.5mW (typ.)
- Flow-Through or Pipelined output mode on either port via the FT/PIPE pins
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic

- Full synchronous operation on both ports
 - 4ns setup to clock and 0ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 6.5ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 12ns cycle time, 83MHz operation in Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100-pin Thin Quad Flatpack (TQFP)

Functional Block Diagram



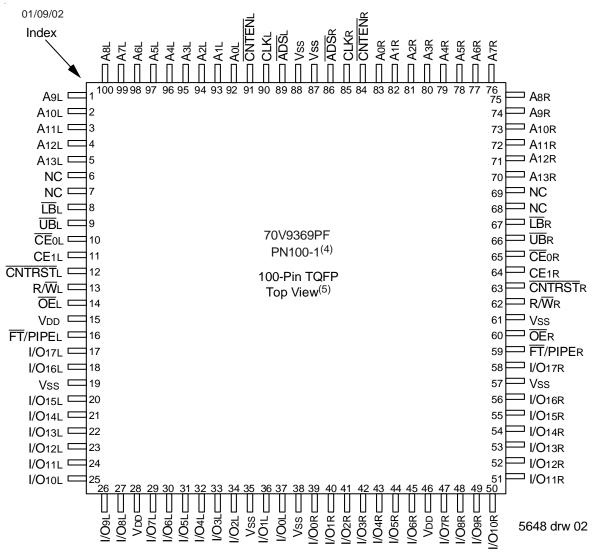
OCTOBER 2008

Description:

The IDT70V9369 is a high-speed 16K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT70V9369 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}$ 0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 500mW of power.





- 1. All VDD pins must be connected to power supply.
- 2. All Vss pins must be connected to ground.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names			
CEOL, CE1L	CEOR, CE1R	Chip Enables ⁽²⁾			
R/WL	R/WR	Read/Write Enable			
ŌĒL	OE R	Output Enable			
A0L - A13L	A0R - A13R	Address			
I/O0L - I/O17L	I/O0R - I/O17R	Data Input/Output			
CLKL	CLKR	Clock			
ŪBL .	UB R	Upper Byte Select ⁽¹⁾			
<u>LB</u> L	LB R	Lower Byte Select ⁽¹⁾			
ADSL	ĀDSR	Address Strobe Enable			
CNTENL	CNTENR	Counter Enable			
CNTRSTL	<u>CNTRST</u> R	Counter Reset			
FT/PIPEL	FT/PIPER	Flow-Through / Pipeline			
V	DD	Power (3.3V)			
V	SS	Ground (0V)			

5648 tbl 01

- LB and UB are single buffered regardless of state of FT/PIPE.
 CEo and CE1 are single buffered when FT/PIPE = VIL, CEo and CE1 are double buffered when FT/PIPE = VIH, i.e., the signals take two cycles to deselect.

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	<u>CE</u> ₀	CE1	ŪB	ĪΒ	R/W	Upper Byte I/O ₉₋₁₇ ⁽⁴⁾	Lower Byte I/O ₀₋₈ ⁽⁵⁾	MODE	
Х	\uparrow	Н	Χ	Х	Х	Χ	High-Z	High-Z	Deselected-Power Down	
Х	1	Χ	L	Х	Χ	Χ	High-Z	High-Z	Deselected-Power Down	
Х	1	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected	
Х	1	L	Н	L	Н	L	DATAIN	DATAIN High-Z Write to Upper Byte Only		
Х	1	L	Н	Н	L	L	High-Z	DATAIN	Write to Lower Byte Only	
Х	1	L	Н	L	L	L	DATAIN	DATAIN	Write to Both Bytes	
L	1	L	Н	L	Н	Н	DATAout	High-Z	Read Upper Byte Only	
L	1	L	Н	Н	L	Н	High-Z	DATAout	Read Lower Byte Only	
L	\uparrow	L	Н	L	L	Н	DATAout	DATAout	Read Both Bytes	
Н	Χ	L	Н	L	L	Χ	High-Z	High-Z	Outputs Disabled	

5648 tbl 02

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care. 2. ADS, CNTEN, CNTRST = X.
- 3. $\overline{\text{OE}}$ is an asynchronous input signal.

Truth Table II—Address Counter Control (1,2,6)

Address	Previous Internal Address	Internal Address Used	CLK ⁽⁶⁾	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
An	Х	An	↑	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
Х	An	An + 1	1	Н	L ⁽⁵⁾	Н	Dvo(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	1	Н	Н	Н	Dvo(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	A 0	1	Χ	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0

NOTES:

5648 tbl 03

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care. 2. \overline{CE}_0 , \overline{LB} , \overline{UB} , and \overline{OE} = VIL; CE1 and R/ \overline{W} = VIH.
- 3. Outputs configured in Flow-Through Output mode; if outputs are in Pipelined mode the data out will be delayed by one cycle.
- 4. ADS and CNTRST are independent of all other signals including CEo, CE1, UB and LB.
- 5. The address counter advances if $\overline{\text{CNTEN}} = \text{ViL}$ on the rising edge of CLK, regardless of all other signals including $\overline{\text{CE}}_0$, CE₁, $\overline{\text{UB}}$ and $\overline{\text{LB}}$.
- 6. While an external address is being loaded ($\overline{ADS} = VIL$), $R\overline{W} = VIH$ is recommended to ensure data is not written arbitrarily.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature ⁽¹⁾	GND	V _{DD}
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V

NOTES:

5648 tbl 04

1. This is the parameter Ta. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
V _{DD}	Supply Voltage	3.0	3.3	3.6	V
Vss	Ground	0	0	0	V
Vн	Input High Voltage	2.0V	_	V _{DD} +0.3V ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	V

5648 tbl 05

NOTES:

- 1. VIL > -1.5V for pulse width less than 10 ns.
- 2. VTERM must not exceed V_{DD} +0.3V.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS ⁽³⁾	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	۰C
NuT	Junction Temperature	+150	۰C
Іоит	DC Output Current	50	mA

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed VDD +0.3V.
- 3. Ambient Temperature Under DC Bias. No AC Conditions. Chip deselect.

Capacitance⁽¹⁾

 $(TA = +25^{\circ}C, f = 1.0MHz)$

	Symbol	Parameter	Conditions	Max.	Unit
	CIN	Input Capacitance	VIN = 0V	9	pF
ſ	Cout ⁽²⁾	Output Capacitance	Vout = 0V	10	pF

NOTES:

5648 tbl 07

- 1. These parameters are determined by device characterization, but are not production tested.
- 2. Cout also references Ci/o.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 0.3V)

				70V9369L		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit	
LI	Input Leakage Current ⁽¹⁾	$V_{DD} = 3.6V$, $V_{IN} = 0V$ to V_{DD}	_	5	μA	
luo	Output Leakage Current	$\overline{\text{CE}}\text{O} = \text{ViH or CE1} = \text{ViL, Vout} = \text{OV to VdD}$	_	5	μA	
Vol	Output Low Voltage	IoL = +4mA	_	0.4	V	
Voh	Output High Voltage	IoH = -4mA	2.4	_	V	

NOTE:

5648 tbl 08

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽³⁾ (VDD = 3.3V ± 0.3V)

						369L6 I Only	Co	369L7 m'l Ind		369L9 I Only		69L12 Only	
Symbol	Parameter	Test Condition	Versio	n	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
loo	Dynamic Operating	CEL and CER= VIL,	COM'L	L	220	350	200	290	180	225	150	205	mA
	Current (Both Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	L		_	200	335		_	_	_	
ISB1	Standby Current	CEL = CER = VIH	COM'L	L	70	130	65	100	50	65	40	50	mA
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	L		_	65	115	_	_	_	_	
ISB2	Standby		COM'L	L	150	250	140	210	110	150	100	140	mA
	Current (One Port - TTL Level Inputs)	CE"B" = VIH ⁽⁵⁾ Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	L	_	_	140	240	_	_	_	_	
ISB3	Full Standby	Both Ports CEL and	COM'L	L	0.4	5	0.4	5	0.4	5	0.4	5	mA
	Current (Both Ports - CMOS Level Inputs)	$\overline{CER} \ge V_{DD} - 0.2V,$ $V_{IN} \ge V_{DD} - 0.2V$ or $V_{IN} \le 0.2V, f = 0^{(2)}$	IND	L	_	_	0.4	15	-	_		_	
ISB4	Full Standby	<u>CE</u> "A" ≤ 0.2V and	COM'L	L	140	240	130	200	100	140	90	130	mA
	Current (One Port - CMOS Level Inputs)	$\begin{array}{l} \overline{\text{CE}}\text{"B"} \overset{>}{\geq} \text{V}_{\text{DD}} - 0.2 \text{V}^{(5)} \\ \text{V}\text{IN} \overset{>}{\geq} \text{V}_{\text{DD}} - 0.2 \text{V} \text{ or} \\ \text{V}\text{IN} \overset{<}{\leq} 0.2 \text{V}, \text{ Active Port,} \\ \text{Outputs Disabled, } f = f\text{MAX}^{(1)} \end{array}$	IND	L			130	230		_		_	

5648 tbl 09

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, $TA = 25^{\circ}C$ for Typ, and are not production tested. IDD DC(f=0) = 90mA (Typ).
- 5. $\overline{\text{CE}}\text{x} = \text{Vil means } \overline{\text{CE}}\text{ox} = \text{Vil and CE1x} = \text{ViH}$
 - $\overline{CE}x = VIH \text{ means } \overline{CE}_0x = VIH \text{ or } CE_1x = VIL$
 - $\overline{CE}x \leq 0.2V$ means $\overline{CE}_0x \leq 0.2V$ and CE1x $\geq V_{\text{DD}}$ 0.2V
 - $\overline{\text{CE}}$ x \geq V_{DD} 0.2V means $\overline{\text{CE}}$ 0x \geq V_{DD} 0.2V or CE1x \leq 0.2V
 - "X" represents "L" for left port or "R" for right port.

^{1.} At $V_{DD} \leq 2.0V$ input leakages are undefined.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

5648 tbl 10

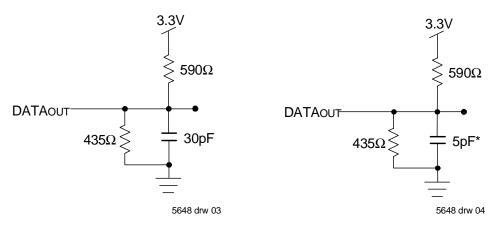


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz).
*Including scope and jig.

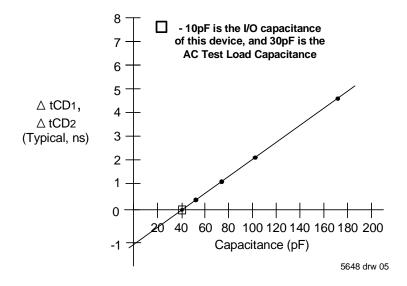


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3)}$ (VDD = 3.3V ± 0.3V, TA = 0°C to +70°C)

	and Write Cycle Timing)(3) (Vbb	70V9	9369L6 'I Only	1	369L7 I Only Ind	70V9	369L9 I Only	70V93	369L12 I Only	
Symbol	Parameter	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Мах.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	19	_	22	_	25	_	30	_	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	10	_	12	_	15	_	20	_	ns
tcH1	Clock High Time (Flow-Through) ⁽²⁾	6.5	_	7.5	_	12	_	12	_	ns
tcl1	Clock Low Time (Flow-Through) ⁽²⁾	6.5	_	7.5	_	12	_	12	_	ns
tch2	Clock High Time (Pipelined) ⁽²⁾	4	_	5	_	6	_	8	_	ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	4	_	5	_	6	_	8	_	ns
tr	Clock Rise Time		3		3		3		3	ns
tr	Clock Fall Time		3		3		3		3	ns
tsa	Address Setup Time	3.5	_	4	_	4	_	4		ns
tha	Address Hold Time	0	_	0	_	1	_	1		ns
tsc	Chip Enable Setup Time	3.5	_	4	_	4	_	4		ns
thc	Chip Enable Hold Time	0	_	0	_	1	_	1		ns
tsw	R/W Setup Time	3.5	_	4	_	4	_	4	_	ns
thw	R/W Hold Time	0	_	0	_	1	_	1		ns
tsd	Input Data Setup Time	3.5	_	4	_	4	_	4	_	ns
thd	Input Data Hold Time	0	_	0	_	1	_	1		ns
tsad	ADS Setup Time	3.5	_	4	_	4	_	4		ns
thad	ADS Hold Time	0	_	0	_	1	_	1	_	ns
tscn	CNTEN Setup Time	3.5	_	4	_	4	_	4	_	ns
thcn	CNTEN Hold Time	0	_	0	_	1	_	1	_	ns
tsrst	CNTRST Setup Time	3.5	_	4	_	4	_	4	_	ns
thrst	CNTRST Hold Time	0	_	0	_	1	_	1	_	ns
toe	Output Enable to Data Valid		6.5		7.5		9	_	12	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	2	_	ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	1	7	ns
tcd1	Clock to Data Valid (Flow-Through) ⁽²⁾		15		18		20		25	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		6.5		7.5		9	_	12	ns
toc	Data Output Hold After Clock High	2	_	2	_	2	_	2	_	ns
tckhz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2	_	2	_	2	_	2	_	ns
Port-to-Port D	Delay									
tcwdd	Write Port Clock High to Read Data Delay		24		28		35	_	40	ns
tccs	Clock-to-Clock Setup Time	_	9	_	10		15	_	15	ns

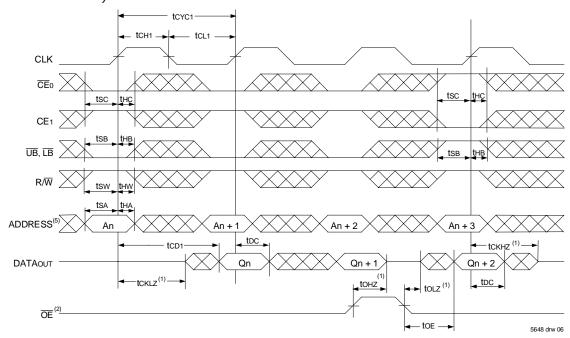
5648 tbl 11

^{1.} Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

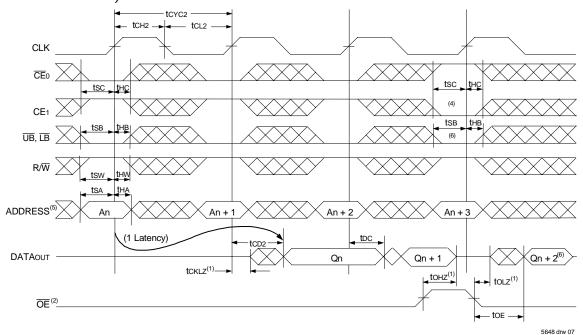
^{2.} The Pipelined output parameters (tcyc2, tcp2) apply to either or both the Left and Right ports when FT/PIPE = ViH. Flow-through parameters (tcyc1, tcp1) apply when $\overline{FT}/PIPE = V_{IL}$ for that port.

^{3.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (\overline{OE}) , $\overline{FT}/PIPER$, and $\overline{FT}/PIPEL$.

Timing Waveform of Read Cycle for Flow-Through Output $(\overline{FT}/PIPE"x" = VIL)^{(3,7)}$

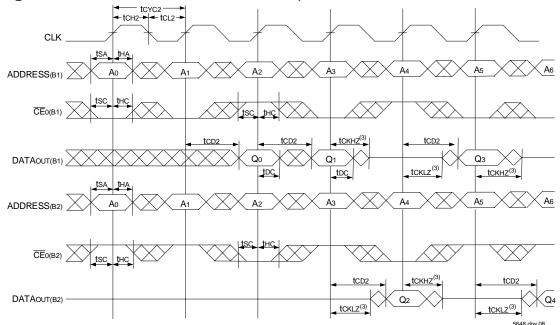


Timing Waveform of Read Cycle for Pipelined Operation $(\overline{FT}/PIPE"x" = VIH)^{(3,7)}$



- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = VIL$, \overline{CNTEN} and $\overline{CNTRST} = VIH$.
- 4. The output is disabled (High-Impedance state) by $\overline{\text{CE}}_0 = \text{V}_{\text{IH}}$, $\overline{\text{CE}}_1 = \text{V}_{\text{IL}}$, $\overline{\text{UB}} = \text{V}_{\text{IH}}$, or $\overline{\text{LB}} = \text{V}_{\text{IH}}$ following the next rising edge of the clock. Refer to Notes under Pin Names Table.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 6. If UB or LB was HIGH, then the Upper Byte and/or Lower Byte of DATAouT for Qn + 2 would be disabled (High-Impedance state).
- 7. "X' here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read (1,2)

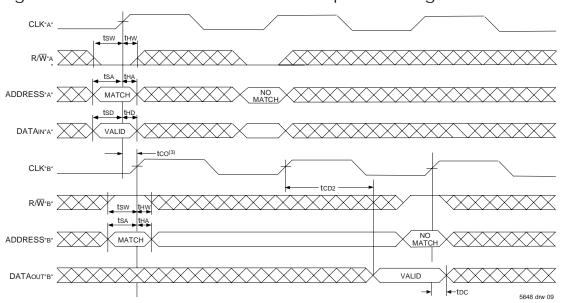


NOTES:

- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9369 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 5. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpb.

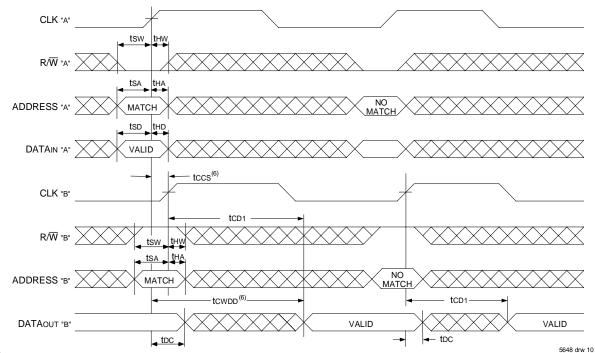
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1, tcwpb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

Timing Waveform of Left Port Write to Pipelined Right Port Read (1,2,4)



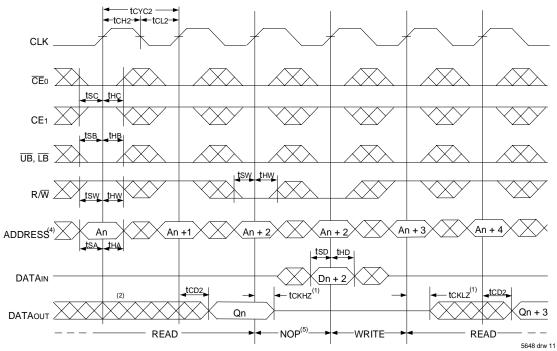
- 1. $\overline{CE_0}$, $\overline{BE_n}$, and $\overline{ADS} = VIL$; CE1, \overline{CNTEN} , and $\overline{REPEAT} = VIH$.
- 2. \overline{OE} = VIL for Port "B", which is being read from. \overline{OE} = VIH for Port "A", which is being written to.
- 3. If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc2 + tcp2).
- 4. All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A"

Timing Waveform with Port-to-Port Flow-Through Read^(4,5,7)

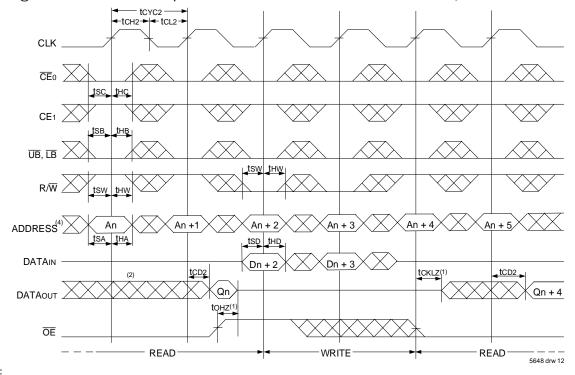


- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9369 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/ \overline{W} , \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
 4. CEo, UB, LB, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH.
- 5. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpp. If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb1. tcwbb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** = VIL)⁽³⁾



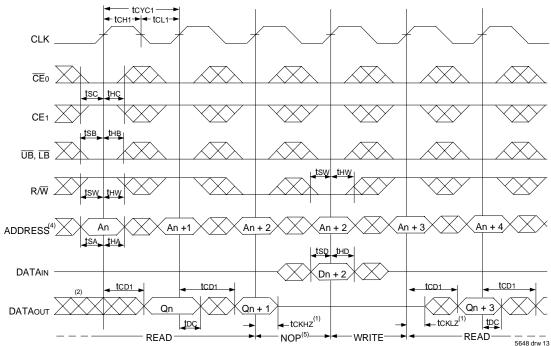
Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽³⁾



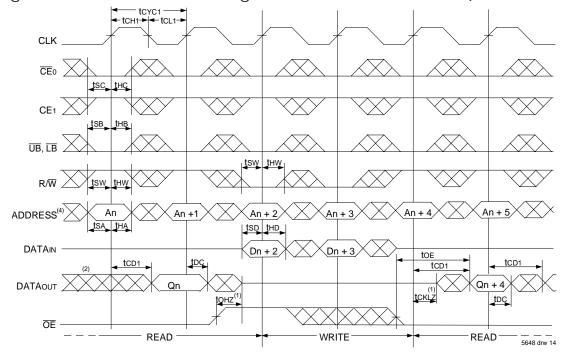
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. CEo, UB, LB, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".

 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** = VIL)⁽³⁾

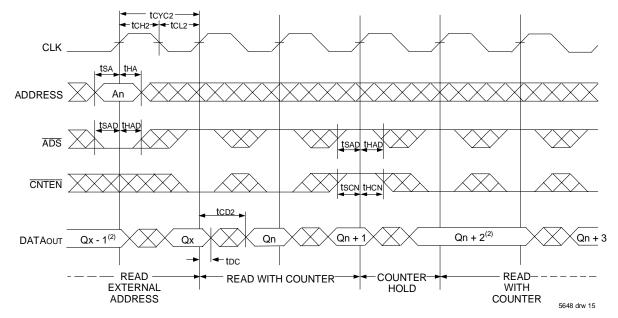


Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽³⁾

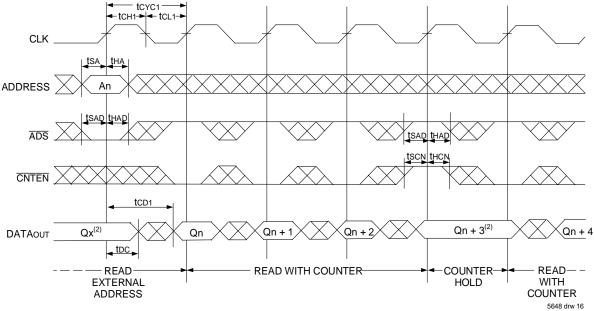


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; \overline{CE}_1 , \overline{CNTEN} , and \overline{CNTRST} = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since \overline{ADS} = V_{IL} constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

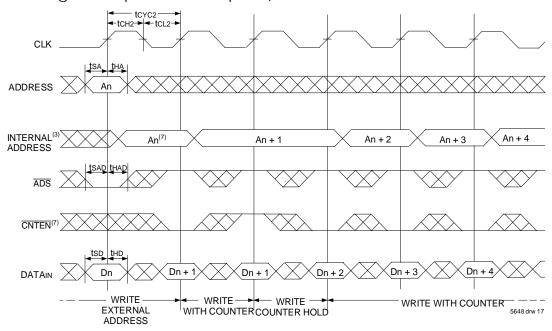


Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾

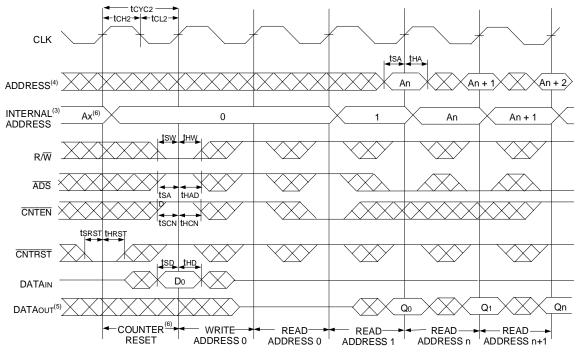


- 1. $\overline{CE_0}$, \overline{OE} , \overline{UB} , and \overline{LB} = V_{IL}; CE₁, R/ \overline{W} , and \overline{CNTRST} = V_{IH}.
- 2. If there is no address change via ADS = VIL (loading a new address) or CNTEN = VIL (advancing the address), i.e. ADS = VIH and CNTEN = VIH, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



- 1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and R/\overline{W} = V_{IL}; CE₁ and \overline{CNTRST} = V_{IH}.
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = VIL$ and equals the counter output when $\overline{ADS} = VIH$.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = V_{IL} advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance.
 The 'An +1' Address is written to during this cycle.

Functional Description

The IDT70V9369 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

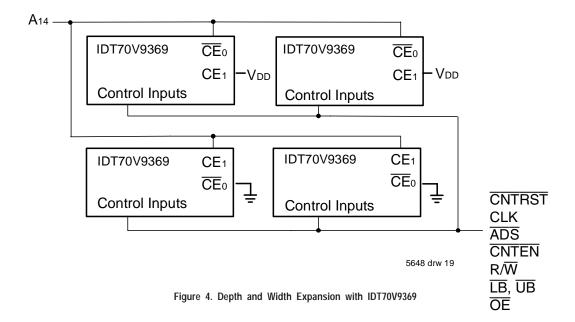
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to staff the operation of the address counters for fast interleaved memory applications.

 $\overline{\text{CE}}_0 = \text{VIL}$ and $\text{CE}_1 = \text{VIH}$ for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9369's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}_0 = \text{VIL}$ and $\text{CE}_1 = \text{VIH}$ to re-activate the outputs.

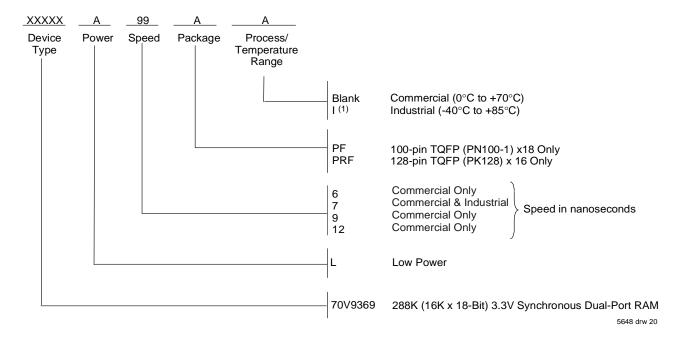
Depth and Width Expansion

The IDT70V9369 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70V9369 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 36-bit or wider applications.



Ordering Information



NOTE:

1. Contact your local sales office for industrial temp range for other speeds, packages and powers.

Datasheet Document History

01/08/02: Initial Public Release

10/11/04: Removed "Preliminary" status

Page 4 Updated Truth Table II

Updated Absolute Maximum Ratings

Updated Capacitance table

Page 5 Added 6ns speed grade and 7ns I-temp, removed 9ns I-temp and updated DC power numbers

in the DC Electrical Characteristics Table

Page 7 Added 6ns speed grade and 7ns I-temp and removed 9ns I-temp AC timing numbers

from the AC Electrical Characteristics Table Updated to E for 7ns and 9ns speed grades

Page 9 Added Timing Waveform of Left Port Write to Pipelined Right Port Read

Page 16 Added 6ns speed grade and 7ns I-temp and removed 9ns I-temp to ordering information

Page 1 & 16 Replaced old тм logo with new тм logo

10/23/08: Page 16 Removed "IDT" from orderable part number



CORPORATE HEADQUARTERS

6024 Silver Creek Valley Road San Jose, CA 95138 for SALES:

800-345-7015 or 408-284-8200

fax: 408-284-2775 www.idt.com for Tech Support: 408-284-2794 DualPortHelp@idt.com

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